Hits	Search Text	

L Number	Hits	Search Text	DB	Time stamp
1	0	438/257,263, 264,762,763.ccls. and	USPAT;	2003/11/29
-		(memory adj cell) and (oxide adj layer)	US-PGPUB;	16:05
		and (floating adj gate) and (dielectric	EPO; JPO;	
		adj layer) and (control adj gate) and	DERWENT	
		((oxide adj layer) with ("40" adj		
	_	angstroms))		
2	0	100, 00, 100, 00, 100, 100, 100, 100,	USPAT;	2003/11/29
ĺ		(memory adj cell) and (oxide adj layer)	US-PGPUB; EPO; JPO;	16:05
		and (floating adj gate) and (dielectric adj layer) and (control adj gate) and	DERWENT	
		(oxide adj layer)	Danie III	ļ.
3	0	l	USPAT;	2003/11/29
*		(memory adj cell) and (oxide adj layer)	US-PGPUB;	16:05
		and (floating adj gate) and (dielectric	EPO; JPO;	
		adj layer) and (control adj gate)	DERWENT	
-	790596		USPAT;	2003/11/26
		floating adj gate and dielectric adj	US-PGPUB;	14:01
		layer and control gate	EPO; JPO;	
	1819	memory adj cell and oxide adj layer and	DERWENT USPAT;	2003/07/10
-	1019	floating adj gate and dielectric adj	US-PGPUB;	14:38
		layer and control adj gate	EPO; JPO;	
ŀ			DERWENT	
-	53		USPAT;	2003/07/11
		floating adj gate and dielectric adj	US-PGPUB;	19:01
1		layer and control adj gate) and oxide adj	EPO; JPO;	ĺ
		layer with "50" adj angstroms	DERWENT	/
-	791060		USPAT;	2003/07/10
	1	floating adj gate and dielectric adj	US-PGPUB; EPO; JPO;	17:10
		layer and control gate	DERWENT	
_	0	(memory adj cell and oxide adj layer and	USPAT;	2003/07/11
	Ĭ	floating adj gate and dielectric adj	US-PGPUB;	19:02
		layer and control adj gate) and oxide adj	EPO; JPO;	
		layer with "50" adj angstroms and .25 adj	DERWENT	
	_	micron adj gate		
-	43		USPAT;	2003/11/13
		floating adj gate and dielectric adj layer and control adj gate) and oxide adj	US-PGPUB; EPO; JPO;	11:11
		layer with "50" adj angstroms and .25 or	DERWENT	
	1	quarter adj micron adj gate	DERWENT	
-	l 0		USPAT;	2003/07/11
		floating adj gate and dielectric adj	US-PGPUB;	19:04
		layer and control adj gate) and oxide adj	EPO; JPO;	
	1	layer with "50" adj angstroms and (.25 or	DERWENT	
	1	quarter) adj micron	IICDAM.	2003/07/12
-	15	(memory adj cell and oxide adj layer and floating adj gate and dielectric adj	USPAT; US-PGPUB;	11:35
		layer and control adj gate) and (.25 or	EPO; JPO;	-1.55
		quarter) adj micron	DERWENT	
_	0		USPAT;	2003/07/11
		floating adj gate and dielectric adj	US-PGPUB;	19:28
	1	layer and control adj gate) and oxide adj	EPO; JPO;	,
		layer with "50" adj angstroms and (.25 or	DERWENT	
		quarter) adj micron	IICDAM.	2003/07/12
-	0	(memory adj cell and oxide adj layer and floating adj gate and dielectric adj	USPAT; US-PGPUB;	2003/07/12
		layer and control adj gate) and oxide adj	EPO; JPO;	11.56
		layer with "50" adj angstroms and (.18 or	DERWENT	
		quarter) adj micron		
-	0	(memory adj cell and oxide adj layer and	USPAT;	2003/07/12
		floating adj gate and dielectric adj	US-PGPUB;	11:33
		layer and control adj gate) and oxide adj	EPO; JPO;	
		layer with "50" adj angstroms and (.18)	DERWENT	
	_	adj micron	HCDym.	2003/07/12
-	0	(memory adj cell and oxide adj layer and floating adj gate and dielectric adj	USPAT; US-PGPUB;	11:33
		layer and control adj gate) and (.18) adj	EPO; JPO;	-1.55
		micron	DERWENT	
	L		,	

-	0	(memory adj cell and oxide adj layer and floating adj gate and dielectric adj	USPAT; US-PGPUB;	2003/07/12 11:33
		layer and control adj gate) and (.15) adj	EPO; JPO;	
_	0	micron (memory adj cell and oxide adj layer and	DERWENT USPAT;	2003/07/12
		floating adj gate and dielectric adj	US-PGPUB;	11:33
		layer and control adj gate) and (.1) adj	EPO; JPO;	
_	0	micron (.1) adj micron	DERWENT USPAT;	2003/07/12
	Ĭ	(.i) adj micron	US-PGPUB;	11:34
			EPO; JPO;	
_	0	(.18) adj micron	DERWENT USPAT;	2003/07/12
	Ĭ	(.10) ddj m1010	US-PGPUB;	11:34
			EPO; JPO;	
_	0	(.25) adj micron	DERWENT USPAT;	2003/07/12
		(120) adj202011	US-PGPUB;	11:34
			EPO; JPO;	
_	0	(memory adj cell and oxide adj layer and	DERWENT USPAT;	2003/07/12
		floating adj gate and dielectric adj	US-PGPUB;	11:35
		layer and control adj gate) and (.25) adj	EPO; JPO; DERWENT	
_	15	micron (memory adj cell and oxide adj layer and	USPAT;	2003/07/12
		floating adj gate and dielectric adj	US-PGPUB;	11:36
		layer and control adj gate) and (.25 or quarter) adj micron	EPO; JPO; DERWENT	
i –	0	(memory adj cell and oxide adj layer and	USPAT;	2003/07/12
		floating adj gate and dielectric adj	US-PGPUB;	11:36
		layer and control adj gate) and (.25) adj	EPO; JPO; DERWENT	
_	43	438/257.CCLS. AND (memory adj cell and	USPAT;	2003/07/13
		oxide adj layer and floating adj gate and	US-PGPUB;	16:25
	1	dielectric adj layer and control adj gate) and oxide adj layer with "50" adj	EPO; JPO; DERWENT	
		angstroms and .25 or quarter adj micron		
	43	adj gate 257/315,316.CCLS. AND 438/257.CCLS. AND	USPAT;	2003/07/13
-	43	(memory adj cell and oxide adj layer and	US-PGPUB;	16:26
		floating adj gate and dielectric adj	EPO; JPO;	
		layer and control adj gate) and oxide adj layer with "50" adj angstroms and .25 or	DERWENT	
		quarter adj micron adj gate		
-	48	memory adj cell and oxide adj layer and	USPAT; US-PGPUB;	2003/11/13 12:16
		floating adj gate and dielectric adj layer and control adj gate and oxide adj	EPO; JPO;	12:16
		layer with "50" adj angstroms and .25 or	DERWENT	
_	1797	quarter adj micron adj gate memory adj cell and oxide adj layer and	USPAT;	2003/11/13
-	1/3/	floating adj gate and dielectric adj	US-PGPUB;	12:08
		layer and control adj gate and oxide adj	EPO; JPO;	
		layer and "50" adj angstroms and .25 or quarter adj micron	DERWENT	
-	0	(memory adj cell) and (oxide adj layer)	USPAT;	2003/11/13
		and (floating adj gate) and (dielectric adj layer) and (control adj gate) and	US-PGPUB; EPO; JPO;	12:22
		((oxide adj layer) with ("50" adj	DERWENT	
		angstroms) and (.25 or quarter adj micron		
_	57	adj gate)) (memory adj cell) and (oxide adj layer)	USPAT;	2003/11/13
		and (floating adj gate) and (dielectric	US-PGPUB;	18:04
		adj layer) and (control adj gate) and ((oxide adj layer) with ("50" adj	EPO; JPO; DERWENT	
		angstroms))	DEKMENT	
-	0	257/315,316.ccls and (memory adj cell)	USPAT;	2003/11/13
		and (oxide adj layer) and (floating adj gate) and (dielectric adj layer) and	US-PGPUB; EPO; JPO;	16:38
		(control adj gate) and ((oxide adj layer)	DERWENT	
		with ("50" adj angstroms))		

_	9	438/264,762,763.ccls. and (memory adj cell) and (oxide adj layer) and (floating	USPAT; US-PGPUB;	2003/11/13 18:01
		adj gate) and (dielectric adj layer) and (control adj gate) and ((oxide adj layer) with ("50" adj angstroms))	EPO; JPO; DERWENT	
-	0	438/264,762,763.ccls. and (memory adj cell) and (oxide adj layer) and (floating	USPAT; US-PGPUB;	2003/11/29 16:04
		adj gate) and (dielectric adj layer) and (control adj gate) and ((oxide adj layer)	EPO; JPO; DERWENT	
-	0	with ("23" adj angstroms)) 6515328.pn. and (p adj channel)	USPAT; US-PGPUB;	2003/11/13 17:41
			EPO; JPO; DERWENT	17.41
-	0	6515328.pn. and (p adj channel or positiv\$3 adj dop\$3)	USPAT; US-PGPUB; EPO; JPO;	2003/11/13 17:43
_	0	6515328.pn. and ((p adj channel) or	DERWENT USPAT;	2003/11/13
		(positiv\$3 adj dop\$3))	US-PGPUB; EPO; JPO; DERWENT	17:44
-	0	5852311.pn. and ((p adj channel) or (positiv\$3 adj dop\$3))	USPAT; US-PGPUB;	2003/11/13 17:45
			EPO; JPO; DERWENT	
-	0	5869370.pn. and ((p adj channel) or (positiv\$3 adj dop\$3))	USPAT; US-PGPUB; EPO; JPO;	2003/11/13 17:46
_	0	6515328.pn. and ((p adj channel) or	DERWENT USPAT;	2003/11/13
		(positiv\$3 adj dop\$3))	US-PGPUB; EPO; JPO; DERWENT	17:46
-	0	6383939.pn. and ((p adj channel) or (positiv\$3 adj dop\$3))	USPAT; US-PGPUB;	2003/11/13 17:47
			EPO; JPO; DERWENT	
-	0	6316316.pn. and ((p adj channel) or (positiv\$3 adj dop\$3))	USPAT; US-PGPUB; EPO; JPO;	2003/11/13
-	1	6456535.pn. and ((p adj channel) or (positiv\$3 adj dop\$3))	DERWENT USPAT; US-PGPUB;	2003/11/13 17:48
			EPO; JPO; DERWENT	
-	0	6261906.pn. and ((p adj channel) or (positiv\$3 adj dop\$3))	USPAT; US-PGPUB;	2003/11/13 17:48
_	0	6261906.pn. and ((p adj channel) or	EPO; JPO; DERWENT USPAT;	2003/11/13
		(positiv\$3 same dop\$3))	US-PGPUB; EPO; JPO;	17:49
_	0	5852311.pn. and ((p adj channel) or	DERWENT USPAT;	2003/11/13
		(positiv\$3 same dop\$3))	US-PGPUB; EPO; JPO; DERWENT	17:49
_	0	5869370.pn. and ((p adj channel) or (positiv\$3 same dop\$3))	USPAT; US-PGPUB;	2003/11/13 17:50
	_		EPO; JPO; DERWENT	2002/21/22
_	0	5852311.pn. and ((p adj channel) or (positiv\$3 same dop\$3))	USPAT; US-PGPUB; EPO; JPO;	2003/11/13 17:50
-	o	5869370.pn. and ((p adj channel) or (positiv\$3 same dop\$3))	DERWENT USPAT; US-PGPUB;	2003/11/13 17:50
			EPO; JPO; DERWENT	

-	0	6515328.pn. and ((p adj channel) or (positiv\$3 same dop\$3))	USPAT; US-PGPUB; EPO; JPO;	2003/11/13 17:51
-	0	6316316.pn. and ((p adj channel) or	DERWENT USPAT; US-PGPUB;	2003/11/13 17:51
		(positiv\$3 same dop\$3))	EPO; JPO; DERWENT	17:51
-	1	6456535.pn. and ((p adj channel) or (positiv\$3 same dop\$3))	USPAT; US-PGPUB; EPO; JPO;	2003/11/13 17:51
_	0	6261906.pn. and ((p adj channel) or (positiv\$3 same dop\$3))	DERWENT USPAT; US-PGPUB;	2003/11/13 17:55
_	0	6372651.pn. and ((p adj channel) or	EPO; JPO; DERWENT USPAT;	2003/11/13
		(positiv\$3 same dop\$3))	US-PGPUB; EPO; JPO; DERWENT	17:56
-	0	6383939.pn. and ((p adj channel) or (positiv\$3 same dop\$3))	USPAT; US-PGPUB; EPO; JPO;	2003/11/13
-	0	6515328.pn. and ((p adj channel) or (positiv\$3 same dop\$3))	DERWENT USPAT; US-PGPUB; EPO; JPO;	2003/11/13 17:57
_	0	6316316.pn. and ((p adj channel) or (positiv\$3 same dop\$3))	DERWENT USPAT; US-PGPUB;	2003/11/13 17:57
-	1	6456535.pn. and ((p adj channel) or (positiv\$3 same dop\$3))	EPO; JPO; DERWENT USPAT; US-PGPUB;	2003/11/13 17:57
_	o	6249819.pn. and ((p adj channel) or (positiv\$3 same dop\$3))	EPO; JPO; DERWENT USPAT; US-PGPUB;	2003/11/13 17:58
_	0	20030201477.pn. and ((p adj channel) or	EPO; JPO; DERWENT USPAT;	2003/11/13
		(positiv\$3 same dop\$3))	US-PGPUB; EPO; JPO; DERWENT	17:58
-	0	438/264,762,763.ccls. and (memory adj cell) and (oxide adj layer) and (floating adj gate) and (dielectric adj layer) and (control adj gate) and ((oxide adj layer)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/11/13 18:02
	18	with ("50" adj angstroms)) and ((p adj channel) or (p-channel)) (memory adj cell) and (oxide adj layer)	USPAT;	2003/11/25
	10	and (floating adj gate) and (dielectric adj layer) and (control adj gate) and ((oxide adj layer) with ("50" adj	US-PGPUB; EPO; JPO; DERWENT	13:44
_	303	angstroms)) and ((p-channel) or (p adj channel)) (memory adj cell) and (oxide adj layer)	USPAT;	2003/11/13
		and (floating adj gate) and (dielectric adj layer) and (control adj gate) and ((p-channel) or (p adj channel))	US-PGPUB; EPO; JPO; DERWENT	18:10
-	3	(memory adj cell) and (oxide adj layer) and (floating adj gate) and (dielectric adj layer) and (control adj gate) and	USPAT; US-PGPUB; EPO; JPO;	2003/11/25 14:47
		((oxide adj layer) with ("40" adj angstroms)) and ((p-channel) or (p adj channel))	DERWENT	
_	1	5408115.pn. and ((oxide adj layer) with ("40" adj angstroms)) and ((p-channel) or (p adj channel))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/11/25 14:18





			T 2	0000 /44 /05
-	13	(memory adj cell) and (oxide adj layer)	USPAT;	2003/11/25
		and (floating adj gate) and (dielectric	US-PGPUB;	14:53
		adj layer) and (control adj gate) and	EPO; JPO;	
		((oxide adj layer) with ("30" adj	DERWENT	
		angstroms)) and ((p-channel) or (p adj		
		channel))		
_	13	, ,	USPAT;	2003/11/25
-	13	and (floating adj gate) and (dielectric	US-PGPUB;	14:54
				14.54
		adj layer) and (control adj gate) and	EPO; JPO;	
		((oxide adj layer) with ("23" adj	DERWENT	
		angstroms)) and ((p-channel) or (p adj		1
		channel))		
-	0	6515328.pn. and (p-channel or p adj	USPAT;	2003/11/26
		channel)	US-PGPUB;	14:02
			EPO; JPO;	
			DERWENT	
	l 0	6372651.pn. and (p-channel or p adj	USPAT;	2003/11/26
	ľ	channel)	US-PGPUB;	14:03
		Chamici	EPO; JPO;	
			DERWENT	
		cooper and the shannel on a add	USPAT;	2003/11/26
-		6383939.pn. and (p-channel or p adj		14:04
1		channel)	US-PGPUB;	1 14:04
			EPO; JPO;	
			DERWENT	
-	0	6383939.pn. and (p-channel or p adj	USPAT;	2003/11/26
		channel or p channel)	US-PGPUB;	14:04
	1	-	EPO; JPO;	
			DERWENT	
		l	 	